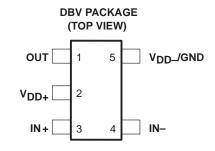
- Output Swing Includes Both Supply Rails
- Low Noise . . . 21 nV/ $\sqrt{\text{Hz}}$ Typ at f = 1 kHz
- Low Input Bias Current . . . 1 pA Typ
- Very Low Power . . . 11 μA Per Channel Typ
- Common-Mode Input Voltage Range Includes Negative Rail
- Wide Supply Voltage Range 2.7 V to 10 V
- Available in the SOT-23 Package
- Macromodel Included

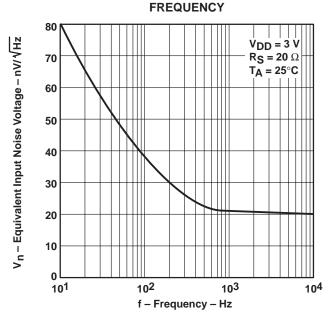
description

The TLV2711 is a single low-voltage operational amplifier available in the SOT-23 package. It consumes only 11 μA (typ) of supply current and is ideal for battery-power applications. Looking at Figure 1, the TLV2711 has a 3-V noise level of 21 nV/ $\sqrt{\text{Hz}}$ at 1 kHz; five times lower than competitive SOT-23 micropower solutions. The device exhibits rail-to-rail output performance for increased dynamic range in single- or split-supply applications. The TLV2711 is fully characterized at 3 V and 5 V and is optimized for low-voltage applications.

The TLV2711, exhibiting high input impedance and low noise, is excellent for small-signal conditioning for high-impedance sources, such as piezoelectric transducers. Because of the micropower dissipation levels combined with 3-V operation, these devices work well in hand-held monitoring and remote-sensing applications. In addition, the rail-to-rail output feature with single or split supplies makes this family a great choice when interfacing with analog-to-digital converters (ADCs).



EQUIVALENT INPUT NOISE VOLTAGE†



† For all curves where $V_{DD} = 5$ V, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3$ V, all loads are referenced to 1.5 V.

Figure 1. Equivalent Input Noise Voltage Versus Frequency

With a total area of 5.6mm², the SOT-23 package only requires one-third the board space of the standard 8-pin SOIC package. This ultra-small package allows designers to place single amplifiers very close to the signal source, minimizing noise pick-up from long PCB traces.

AVAILABLE OPTIONS

	т.	Viemay AT 25°C	PACKAGED DEVICES	SYMBOL	CHIP FORM‡
	TA	V _{IO} max AT 25°C	SOT-23 (DBV)†	STIVIBUL	(Y)
	0°C to 70°C	3 mV	TLV2711CDBV	VAJC	TI V2711Y
1	-40°C to 85°C	3 mV	TLV2711IDBV	VAJI	1642/111

[†]The DBV package available in tape and reel only.

[‡] Chip forms are tested at $T_A = 25^{\circ}C$ only.



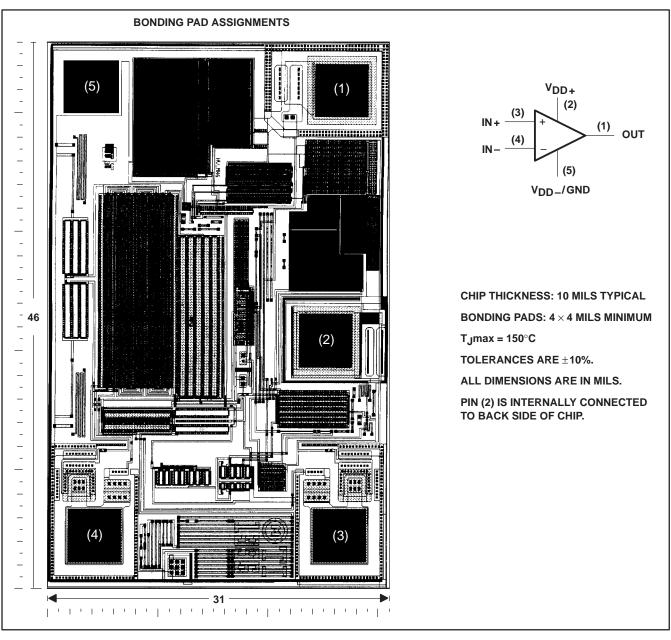
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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TEXAS INSTRUMENTS

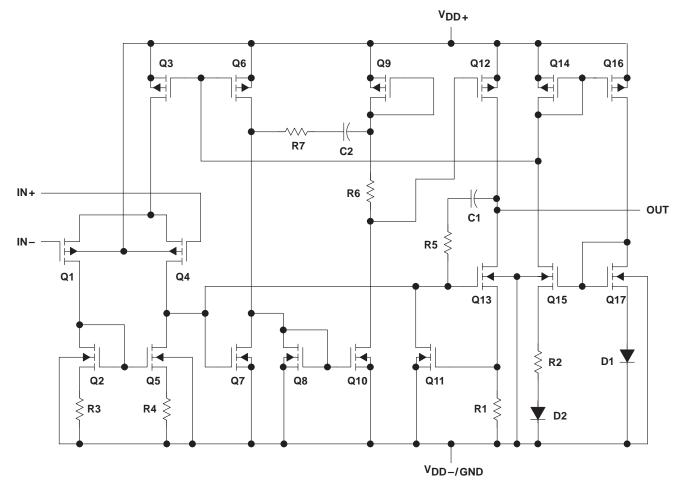
TLV2711Y chip information

This chip, when properly assembled, displays characteristics similar to the TLV2711C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. This chip may be mounted with conductive epoxy or a gold-silicon preform.





equivalent schematic



COMPONENT COUNT [†]						
Transistors	23					
Diodes Resistors	6 11					
Capacitors	2					

[†] Includes both amplifiers and all ESD, bias, and trim circuitry

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V _{DD} (see Note 1)	
Differential input voltage, V _{ID} (see Note 2)	±V _{DD}
Input voltage range, V _I (any input, see Note 1)	0.3 V to V _{DD}
Input current, I _I (each input)	±5 mA
Output current, I _O	±50 mA
Total current into V _{DD+}	±50 mA
Total current out of V _{DD}	±50 mA
Duration of short-circuit current (at or below) 25°C (see Note 3)	unlimited
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T _A : TLV2711C	0°C to 70°C
TLV2711I	
Storage temperature range, T _{Stq}	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: DBV package	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to V_{DD} _.
 - 2. Differential voltages are at the noninverting input with respect to the inverting input. Excessive current flows when input is brought below V_{DD} = 0.3 V.
 - 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{$\Delta$}} \leq 25^{\circ}\mbox{$C$}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING
DBV	150 mW	1.2 mW/°C	96 mW	78 mW

recommended operating conditions

	TLV2711C MIN MAX		TI	UNIT	
			MIN	MAX	UNII
Supply voltage, V _{DD} (see Note 1)	2.7	10	2.7	10	V
Input voltage range, V _I	V_{DD-}	V _{DD+} -1.3	V _{DD} -	V _{DD+} -1.3	V
Common-mode input voltage, V _{IC}	V _{DD} -	V _{DD+} -1.3	V _{DD} _	V _{DD+} -1.3	V
Operating free-air temperature, T _A	0	70	-40	85	°C

NOTE 1: All voltage values, except differential voltages, are with respect to V_{DD} -.



electrical characteristics at specified free-air temperature, $V_{DD} = 3 \text{ V}$ (unless otherwise noted)

	DADAMETED	TEOT COMP	ITIONIO	- +	Т	LV27110	2	Т	LV2711	I	
	PARAMETER	TEST COND	IIIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
VIO	Input offset voltage					0.4	3		0.4	3	mV
αVIO	Temperature coefficient of input offset voltage			Full range		1			1		μV/°C
	Input offset voltage long-term drift (see Note 4)	$V_{DD\pm} = \pm 1.5 \text{ V},$ $V_{O} = 0,$	$V_{IC} = 0$, RS = 50 Ω	25°C		0.003			0.003		μV/mo
IIO	Input offset current			25°C		0.5	60		0.5	60	
10	input onset ourient			Full range			150			150	pА
I _{IB}	Input bias current			25°C			60			60	
'ID	input bido darront			Full range		1	150		1	150	
\/	Common-mode input	11/1-1-5-00/	D- 50.0	25°C	0 to 2	-0.3 to 2.2		0 to 2	-0.3 to 2.2		V
VICR	voltage range	V _{IO} ≤5 mV,	$R_S = 50 \Omega$	Full range	0 to 1.7			0 to 1.7			V
		I _{OH} = -100 μA		25°C		2.94			2.94		
VOH	High-level output			25°C		2.85			2.85		V
	voltage	ΙΟΗ = -250 μΑ		Full range	2.6			2.6			1
		V _{IC} = 1.5 V,	I _{OL} = 50 μA	25°C		15			15		
VOL	Low-level output voltage	V 4.5.V		25°C		150			150		mV
	voltage	V _{IC} = 1.5 V,	$I_{OL} = 500 \mu\text{A}$	Full range			500			500	1
	Large-signal		5 401 ot	25°C	3	7		3	7		
A _{VD}	differential voltage	$V_{IC} = 1.5 \text{ V},$ $V_{O} = 1 \text{ V to 2 V}$	$R_L = 10 \text{ k}\Omega^{\ddagger}$	Full range	1			1			V/mV
	amplification	10-11021	$R_L = 1 M\Omega^{\ddagger}$	25°C		600			600		
r _{i(d)}	Differential input resistance			25°C		10 ¹²			10 ¹²		Ω
r _{i(c)}	Common-mode input resistance			25°C		1012			1012		Ω
Ci(c)	Common-mode input capacitance	f = 10 kHz,		25°C		5			5		pF
z _O	Closed-loop output impedance	f = 7 kHz,	A _V = 1	25°C		200			200		Ω
CMRR	Common-mode	$V_{IC} = 0 \text{ to } 1.7 \text{ V},$	V _O = 1.5 V,	25°C	65	83		65	83		dB
OWINK	rejection ratio	$R_S = 50 \Omega$		Full range	60			60			ub_
ksvr	Supply voltage rejection ratio	V _{DD} = 2.7 V to 8 V,	$V_{IC} = V_{DD}/2$	25°C	80	95		80	95		dB
	(ΔV _{DD} /ΔV _{IO})		,	Full range	80			80			
IDD	Supply current	V _O = 1.5 V,	No load	25°C		11	25	<u> </u>	11	25	μΑ
	11.7			Full range			30			30	F

[†] Full range for the TLV2711C is 0°C to 70°C. Full range for the TLV2711I is – 40°C to 85°C.



[‡]Referenced to 1.5 V

NOTE 4: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150^{\circ}C$ extrapolated to $T_A = 25^{\circ}C$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.

TLV2711, TLV2711Y Advanced LinCMOS™ RAIL-TO-RAIL MICROPOWER SINGLE OPERATIONAL AMPLIFIERS

SLOS196A - AUGUST 1997 - REVISED MARCH 2001

operating characteristics at specified free-air temperature, V_{DD} = 3 V (unless otherwise noted)

	PARAMETER	TEST COND	PAOITI	T. †	Т	TLV2711C		1	LV2711	I	UNIT	
	PARAMETER	TEST COND	IIIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
		V= 44Vt=40V	D. 40 kgt	25°C	0.01	0.025		0.01	0.025			
SR	Slew rate at unity gain	$V_O = 1.1 \text{ V to } 1.9 \text{ V},$ $C_L = 100 \text{ pF}^{\ddagger}$	K[= 10 K22+,	Full range	0.005			0.005			V/μs	
\ <u></u>	Equivalent input noise	f = 10 Hz	z 25°C 80		80		->///					
V _n	voltage	f = 1 kHz		25°C		22			22		nV/√Hz	
V	Peak-to-peak equivalent	f = 0.1 Hz to 1 Hz		25°C		660			660		nV	
V _{N(PP)}	input noise voltage	f = 0.1 Hz to 10 Hz		25°C		880			880		110	
In	Equivalent input noise current			25°C		0.6			0.6		fA/√ Hz	
	Gain-bandwidth product	f = 10 kHz, $C_L = 100 \text{ pF}^{\ddagger}$	$R_L = 10 \text{ k}\Omega^{\ddagger}$,	25°C		56			56		kHz	
ВОМ	Maximum output-swing bandwidth	$V_{O(PP)} = 1 \text{ V},$ $R_{L} = 10 \text{ k}\Omega^{\ddagger},$	$A_V = 1,$ $C_L = 100 \text{ pF}^{\ddagger}$	25°C		7			7		kHz	
φm	Phase margin at unity gain	R _L = 10 kΩ [‡] ,	C _L = 100 pF‡	25°C		56°			56°			
	Gain margin			25°C		20			20		dB	

[†]Full range is -40°C to 85°C.



[‡]Referenced to 1.5 V

electrical characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

				-							
	PARAMETER	TEST COND	SIAONE	т.+	Т	LV27110	0		LV2711	I	UNIT
	FARAIVIE I EK	IESI COND	IIION3	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNII
V _{IO}	Input offset voltage					0.45	3		0.45	3	mV
αVIO	Temperature coefficient of input offset voltage			Full range		0.5			0.5		μV/°C
	Input offset voltage long-term drift (see Note 4)	$V_{DD\pm} = \pm 2.5 \text{ V},$ $V_{O} = 0,$	$V_{IC} = 0$, RS = 50 Ω	25°C		0.003			0.003		μV/mo
I _{IO}	Input offset current			25°C		0.5	60		0.5	60	рA
10	- Input onoct current			Full range			150			150	P/ \
I _{IB}	Input bias current			25°C		1	60		1	60	pА
10				Full range			150			150	<u> </u>
V:	Common-mode input $ V_{IO} \le 5 \text{ mV}$ $R_S = 50 \Omega$		25°C	0 to 4	-0.3 to 4.2		0 to 4	-0.3 to 4.2			
VICR	voltage range	V _{IO} ≤5 mV	RS = 50 Ω	Full range	0 to 3.5			0 to 3.5			V
		I _{OH} = -100 μA		25°C		4.95			4.95		
Vон	High-level output voltage	Jan. 250 A		25°C		4.875			4.875		V
		I _{OH} = -250 μA		Full range	4.6			4.6			
	Low lovel output	$V_{IC} = 2.5 V,$	$I_{OL} = 50 \mu A$	25°C		12			12		
VOL	Low-level output voltage	V _{IC} = 2.5 V,	I _{OL} = 500 μA	25°C		120			120		mV
		V ₁ C = 2.5 V,	-10L = 000 μ/ι	Full range			500			500	
	Large-signal	V _{IC} = 2.5 V,	$R_L = 10 \text{ k}\Omega^{\ddagger}$	25°C	6	12		6	12		
AVD	differential	$V_0 = 1 \text{ V to 4 V}$		Full range	3			3			V/mV
	voltage amplification	_	$R_L = 1 M\Omega^{\ddagger}$	25°C		800			800		
r _{i(d)}	Differential input resistance			25°C		10 ¹²			1012		Ω
r _{i(c)}	Common-mode input resistance			25°C		10 ¹²			10 ¹²		Ω
^C i(c)	Common-mode input capacitance	f = 10 kHz,		25°C		5			5		pF
z _O	Closed-loop output impedance	f = 7 kHz,	A _V = 1	25°C		200			200		Ω
CMRR	Common-mode	$V_{IC} = 0 \text{ to } 2.7 \text{ V},$	V _O = 2.5 V,	25°C	70	83		70	83		dB
OWINK	rejection ratio	R _S = 50 Ω		Full range	70			70			ub
ksvr	Supply voltage rejection ratio	V _{DD} = 4.4 V to 8 V,	$V_{IC} = V_{DD}/2$	25°C	80	95		80	95		dB
	(ΔV _{DD} /ΔV _{IO})	140 1040		Full range	80			80			
I _{DD}	Supply current	V _O = 2.5 V,	No load	25°C		13	25		13	25	μΑ
-טט	Cappi, carroin	.0 = 2.0 *,	.10 1044	Full range			30			30	"'

[†] Full range for the TLV2711C is 0°C to 70°C. Full range for the TLV2711I is – 40°C to 85°C.



[‡]Referenced to 1.5 V

NOTE 5: Typical values are based on the input offset voltage shift observed through 500 hours of operating life test at $T_A = 150$ °C extrapolated to $T_A = 25$ °C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

TLV2711, TLV2711Y Advanced LinCMOS™ RAIL-TO-RAIL MICROPOWER SINGLE OPERATIONAL AMPLIFIERS

SLOS196A - AUGUST 1997 - REVISED MARCH 2001

operating characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

	PARAMETER	TEST COND	ITIONE	- +	TLV2711C		1	LV2711	ı	UNIT		
	PARAWEIER	LESI COND	ITIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
		V- 45V+035V	D. 40 kgt	25°C	0.01	0.025		0.01	0.025			
SR	Slew rate at unity gain	$V_O = 1.5 \text{ V to } 3.5 \text{ V},$ $C_L = 100 \text{ pF}^{\ddagger}$	R[= 10 K22+,	Full range	0.005			0.005			V/μs	
\ <u></u>	Equivalent input noise	f = 10 Hz		25°C 72 72		72		nV/√ Hz				
V _n	voltage	f = 1 kHz		25°C		21			21		nv/√Hz	
V	Peak-to-peak equivalent	f = 0.1 Hz to 1 Hz		25°C		600			600		nV	
V _{N(PP)}	input noise voltage	f = 0.1 Hz to 10 Hz		25°C		800			800		110	
In	Equivalent input noise current			25°C		0.6			0.6		fA/√ Hz	
	Gain-bandwidth product	f = 10 kHz, $C_L = 100 \text{ pF}^{\ddagger}$	$R_L = 10 \text{ k}\Omega^{\ddagger}$,	25°C		65			65		kHz	
Вом	Maximum output-swing bandwidth	$V_{O(PP)} = 2 \text{ V},$ $R_{L} = 10 \text{ k}\Omega^{\ddagger},$	$A_V = 1$, $C_L = 100 \text{ pF}^{\ddagger}$	25°C		7			7		kHz	
φm	Phase margin at unity gain	R _L = 10 kΩ [‡] ,	C _L = 100 pF [‡]	25°C		60°	·		60°			
	Gain margin			25°C		22			22		dB	

[†]Full range is -40°C to 85°C.

electrical characteristics at V_{DD} = 3 V, T_A = 25°C (unless otherwise noted)

	PARAMETER	TES	T CONDITIONS		TI	_V2711\	′	UNIT
	PARAMETER	153	T CONDITIONS		MIN	TYP	MAX	UNII
VIO	Input offset voltage	., ., .,				0.47		mV
IIO	Input offset current	$V_{DD\pm} = \pm 1.5 \text{ V},$ $R_S = 50 \Omega$	$V_O = 0$,	$V_{IC} = 0,$		0.5		рА
I _{IB}	Input bias current	11.5 - 00 22				1		pА
VICR	Common-mode input voltage range	V _{IO} ≤5 mV,	$R_S = 50 \Omega$			-0.3 to 2.2		V
\/ -	High level cutout valtage	I _{OH} = -100 μA				2.94		V
VOH	High-level output voltage	ΙΟΗ = -200 μΑ				2.85		V
\/01	Low-level output voltage	$V_{IC} = 0,$	$I_{OL} = 50 \mu A$			15		mV
VOL	Low-level output voltage	$V_{IC} = 0$,	$I_{OL} = 500 \mu\text{A}$			150		IIIV
Λ	Large-signal differential	V 1 5 V	V 4.V+= 0.V	$R_L = 10 \text{ k}\Omega^{\dagger}$		7		V/mV
AVD	voltage amplification	V _{IC} = 1.5 V,	$V_O = 1 V \text{ to } 2 V$	$R_L = 1 M\Omega^{\dagger}$		600		V/IIIV
r _{i(d)}	Differential input resistance			-		1012		Ω
r _{i(c)}	Common-mode input resistance					1012		Ω
Ci(c)	Common-mode input capacitance	f = 10 kHz				5		pF
z _O	Closed-loop output impedance	f = 7 kHz,	A _V = 1			200		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = 0 \text{ to } 1.7 \text{ V},$	V _O = 1.5 V,	$R_S = 50 \Omega$		83		dB
ksvr	Supply voltage rejection ratio $(\Delta V_{DD}/\Delta V_{IO})$	$V_{DD} = 2.7 \text{ V to 8 V},$	$V_{IC} = V_{DD}/2$,	No load		95		dB
I_{DD}	Supply current	V _O = 1.5 V,	No load			11		μΑ

[†] Referenced to 1.5 V



[‡]Referenced to 1.5 V

electrical characteristics at V_{DD} = 5 V, T_A = 25°C (unless otherwise noted)

PARAMETER		756	TEST CONDITIONS				TLV2711Y			
	PARAMETER	l les	SI CONDITIONS		MIN	TYP	MAX	UNIT		
VIO	Input offset voltage					0.45		mV		
I _{IO}	Input offset current	$V_{DD} \pm = \pm 2.5 \text{ V},$ $R_{S} = 50 \Omega$	$V_{IC} = 0$,	$V_O = 0$,		0.5		рА		
I _{IB}	Input bias current	11/5 = 30 22				1		рА		
VICR	Common-mode input voltage range	V _{IO} ≤5 mV,	R _S = 50 Ω			-0.3 to 4.2		V		
.,	High level systems values	I _{OH} = -100 μA				4.95		V		
VOH	High-level output voltage	I _{OH} = -250 μA				4.875		V		
\/-·	Low lovel output voltage	V _{IC} = 2.5 V,	I _{OL} = 50 μA			12		mV		
VOL	Low-level output voltage	V _{IC} = 2.5 V,	I _{OL} = 500 μA			120		IIIV		
_	Large-signal differential	V 05.V		$R_L = 10 \text{ k}\Omega^{\dagger}$		12		\//\/		
AVD	voltage amplification	$V_{IC} = 2.5 \text{ V},$	$V_O = 1 V \text{ to } 4 V$	$R_L = 1 M\Omega^{\dagger}$		800		V/mV		
r _{i(d)}	Differential input resistance			•		1012		Ω		
r _{i(c)}	Common-mode input resistance					1012		Ω		
^C i(c)	Common-mode input capacitance	f = 10 kHz				5		pF		
z _o	Closed-loop output impedance	f = 7 kHz,	A _V = 1			200		Ω		
CMRR	Common-mode rejection ratio	$V_{IC} = 0 \text{ to } 2.7 \text{ V},$	V _O = 2.5 V,	$R_S = 50 \Omega$		83		dB		
ksvr	Supply voltage rejection ratio (ΔV _{DD} /ΔV _{IO})	V _{DD} = 4.4 V to 8 V,	$V_{IC} = V_{DD}/2,$	No load		95		dB		
I _{DD}	Supply current	V _O = 2.5 V,	No load			13		μА		

[†]Referenced to 1.5 V

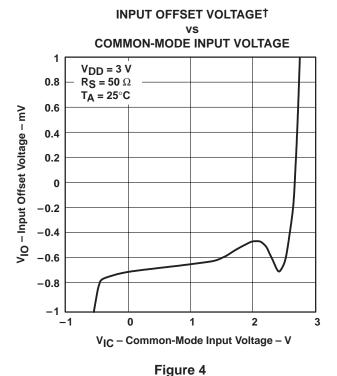
Table of Graphs

			FIGURE
V _{IO}	Input offset voltage	Distribution vs Common-mode input voltage	2, 3 4, 5
αVIO	Input offset voltage temperature coefficient	Distribution	6, 7
I _{IB} /I _{IO}	Input bias and input offset currents	vs Free-air temperature	8
VI	Input voltage	vs Supply voltage vs Free-air temperature	9 10
Vон	High-level output voltage	vs High-level output current	11, 14
VOL	Low-level output voltage	vs Low-level output current	12, 13, 15
V _{O(PP)}	Maximum peak-to-peak output voltage	vs Frequency	16
los	Short-circuit output current	vs Supply voltage vs Free-air temperature	17 18
Vo	Output voltage	vs Differential input voltage	19, 20
AVD	Large-signal differential voltage amplification and phase margin	vs Load resistance vs Frequency vs Free-air temperature	21 22, 23 24, 25
z ₀	Output impedance	vs Frequency	26, 27
CMRR	Common-mode rejection ratio	vs Frequency vs Free-air temperature	28 29
ksvr	Supply-voltage rejection ratio	vs Frequency vs Free-air temperature	30, 31 32
l _{DD}	Supply current	vs Supply voltage	33
SR	Slew rate	vs Load capacitance vs Free-air temperature	34 35
	Large-signal pulse response		36, 37, 38, 39
VO	Inverting small-signal pulse response	vs Time	40, 41
	Small-signal pulse response	7	42, 43
Vn	Equivalent input noise voltage	vs Frequency	44, 45
	Noise voltage (referred to input)	Over a 10-second period	46
THD + N	Total harmonic distortion plus noise	vs Frequency	47
	Gain-bandwidth product	vs Free-air temperature vs Supply voltage	48 49
φm	Phase margin	vs Frequency vs Load capacitance	23, 24 50
	Gain margin	vs Load capacitance	51
B ₁	Unity-gain bandwidth	vs Load capacitance	52



DISTRIBUTION OF TLV2711 INPUT OFFSET VOLTAGE 546 Amplifiers From 1 Wafer Lot $V_{DD} = \pm 1.5 V$ T_A = 25°C 20 Precentage of Amplifiers - % 15 10 5 -0.9 -0.5 -0.1 0.3 -1.3 0.7 1.1 1.5 VIO - Input Offset Voltage - mV

Figure 2



DISTRIBUTION OF TLV2711
INPUT OFFSET VOLTAGE

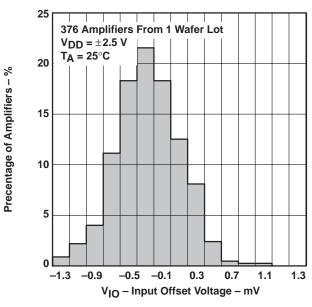


Figure 3

INPUT OFFSET VOLTAGE† VS

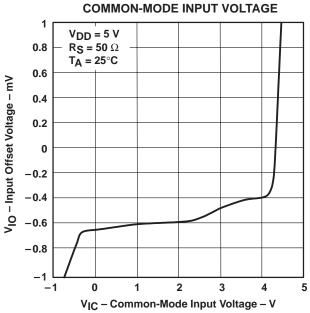
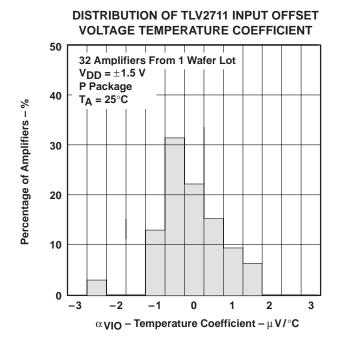


Figure 5

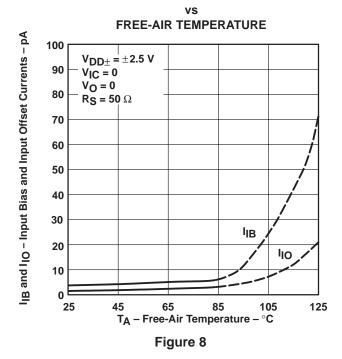
 \dagger For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.







INPUT BIAS AND INPUT OFFSET CURRENTS†



DISTRIBUTION OF TLV2711 INPUT OFFSET VOLTAGE TEMPERATURE COEFFICIENT

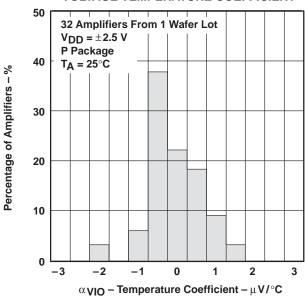
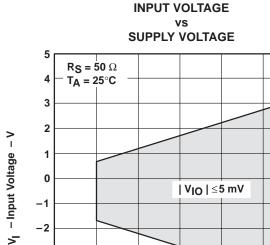


Figure 7



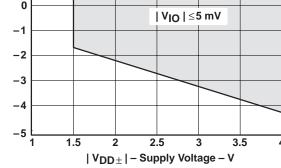
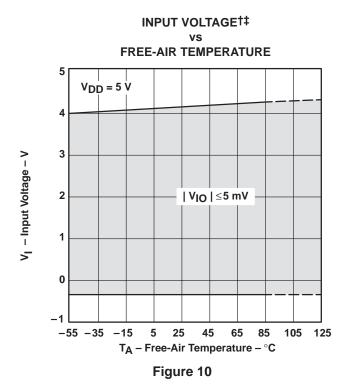
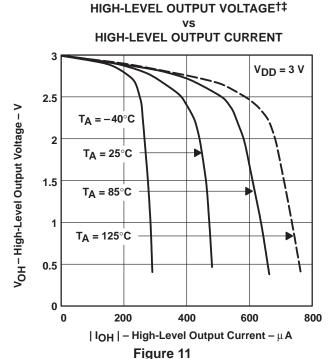


Figure 9

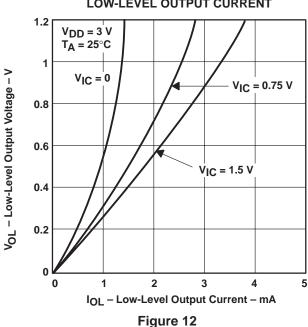
[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



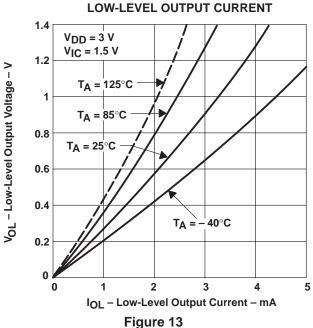








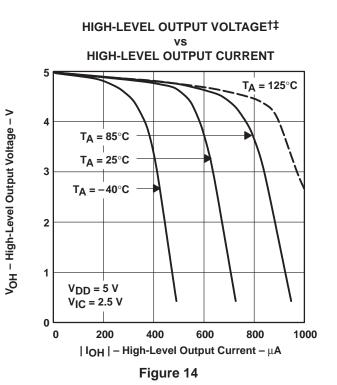
LOW-LEVEL OUTPUT VOLTAGE†‡ VS LOW-LEVEL OUTPUT CURRENT

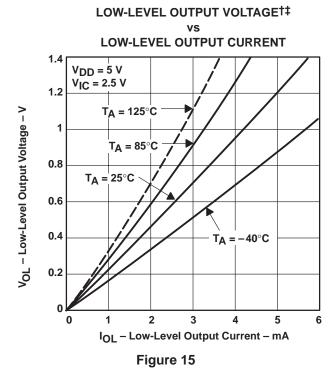


[†]Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

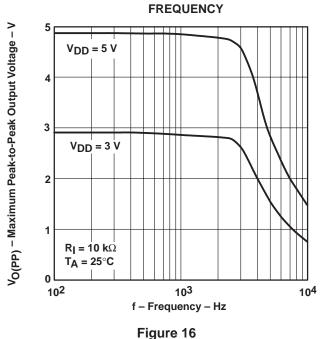
[‡] For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.







MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE‡



SHORT-CIRCUIT OUTPUT CURRENT

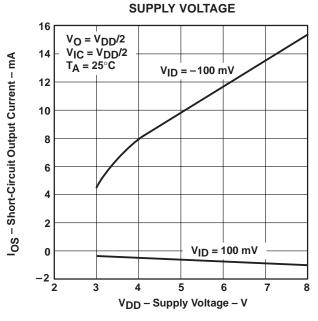


Figure 17

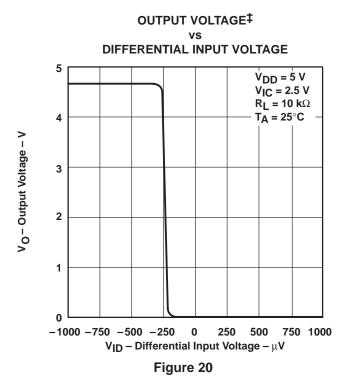
[‡] For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

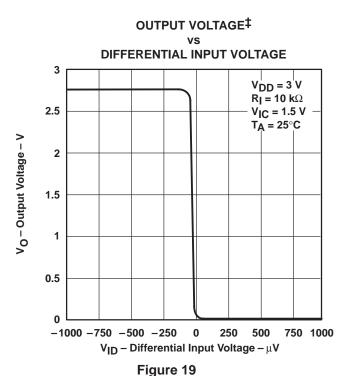


[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

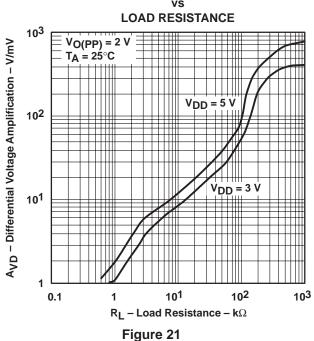
SHORT-CIRCUIT OUTPUT CURRENT†‡ FREE-AIR TEMPERATURE 14 V_{DD} = 5 V V_{IC} = 2.5 V IOS - Short-Circuit Output Current - mA 12 V_O = 2.5 V 10 $V_{ID} = -100 \text{ mV}$ 8 2 $V_{ID} = 100 \text{ mV}$ 0 _ -75 -50 25 75 100 125 TA - Free-Air Temperature - °C

Figure 18





DIFFERENTIAL VOLTAGE AMPLIFICATION[‡]



[†]Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

[‡] For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.



LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE MARGIN†

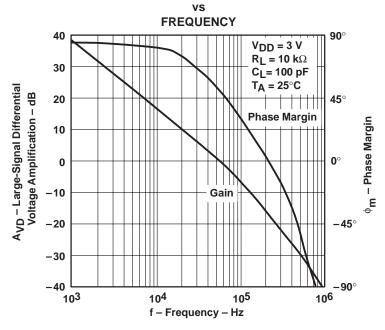


Figure 22

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE MARGIN[†]

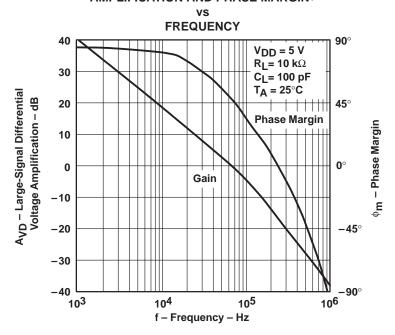
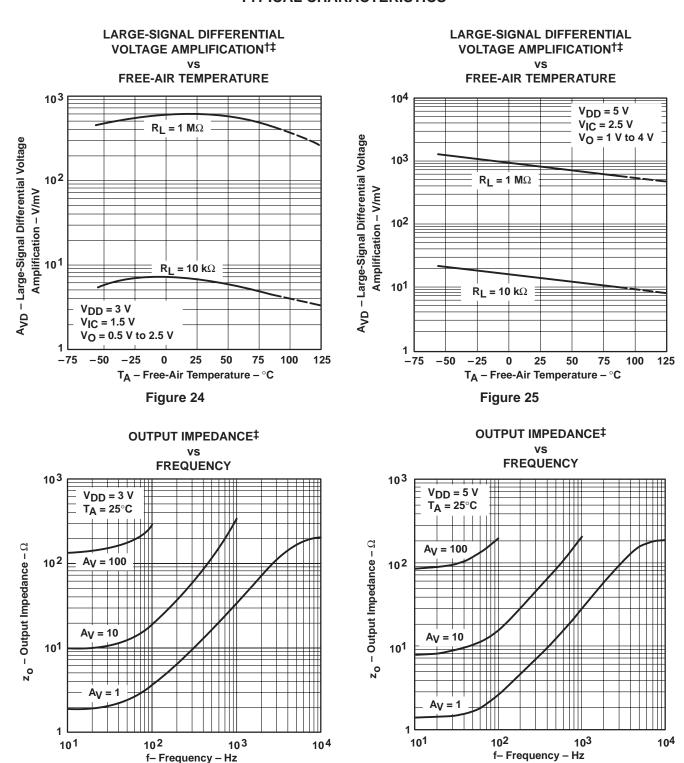


Figure 23

† For all curves where $V_{DD} = 5 \text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3 \text{ V}$, all loads are referenced to 1.5 V.





[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

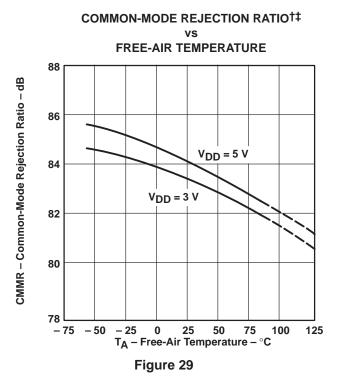
Figure 26

[‡] For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.

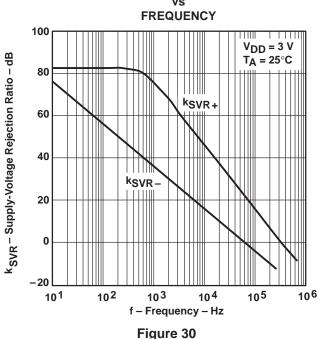


Figure 27

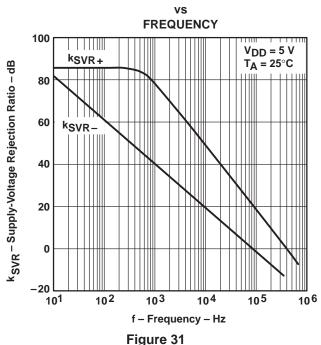
COMMON-MODE REJECTION RATIO† **FREQUENCY** 100 T_A = 25°C CMRR - Common-Mode Rejection Ratio - dB $V_{DD} = 5 V$ $V_0 = 2.5 \text{ V}$ 80 $V_{DD} = 3 V$ 60 $V_0 = 1.5 \text{ V}$ 40 20 101 102 104 f - Frequency - Hz Figure 28



SUPPLY-VOLTAGE REJECTION RATIO† vs



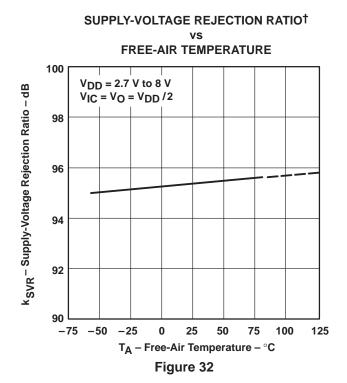
SUPPLY-VOLTAGE REJECTION RATIO†

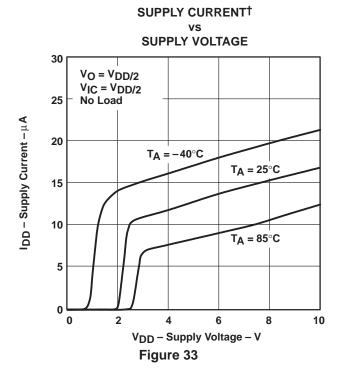


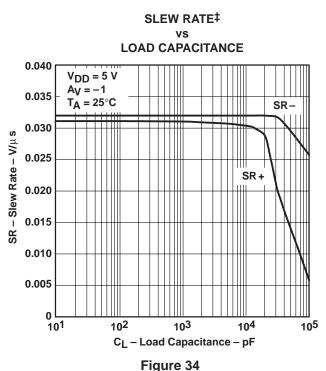
[†] For all curves where $V_{DD} = 5$ V, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3$ V, all loads are referenced to 1.5 V.

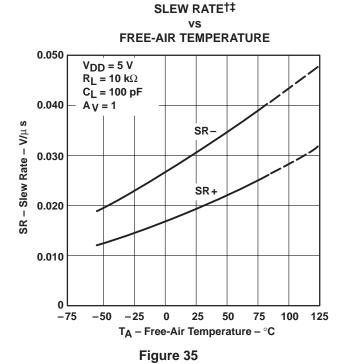
[‡] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.











[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

[‡] For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.



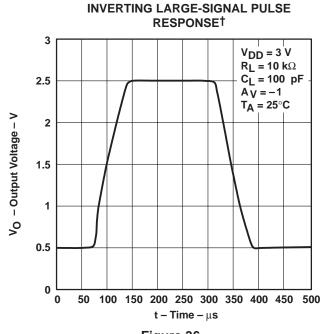
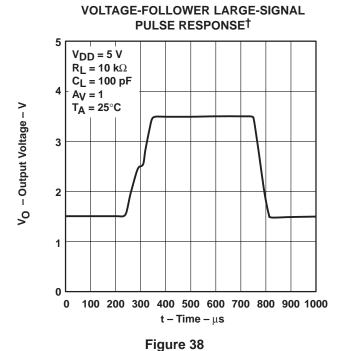
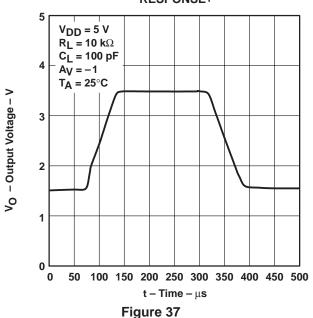


Figure 36



INVERTING LARGE-SIGNAL PULSE RESPONSE†



VOLTAGE-FOLLOWER LARGE-SIGNAL PULSE RESPONSE[†]

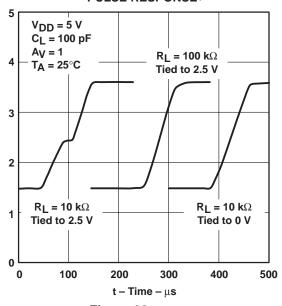
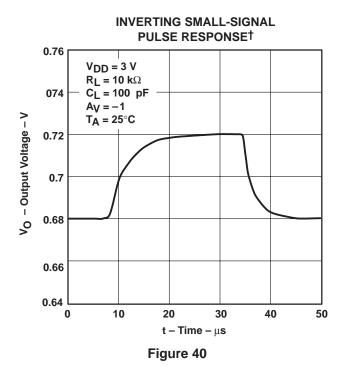


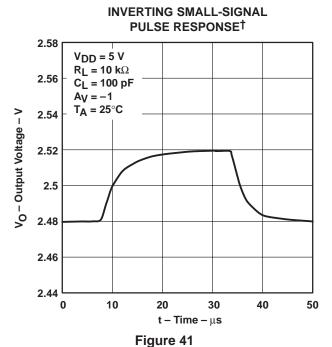
Figure 39

 \dagger For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.



Vo - Output Voltage - V







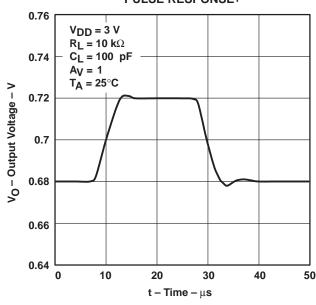


Figure 42

VOLTAGE-FOLLOWER SMALL-SIGNAL PULSE RESPONSE[†]

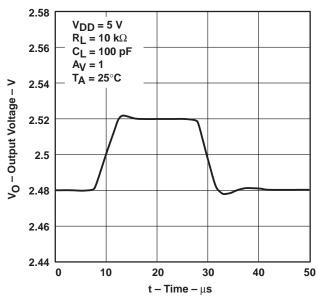
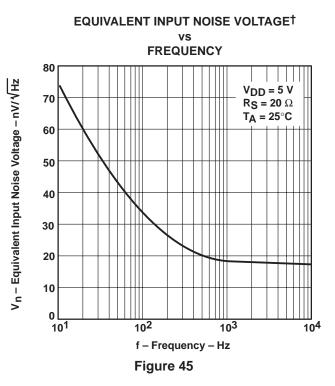


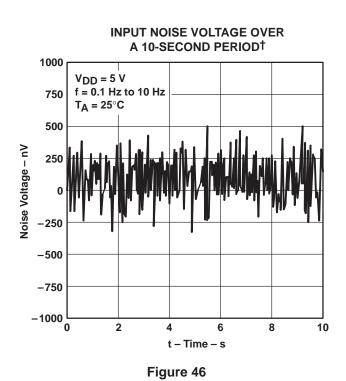
Figure 43

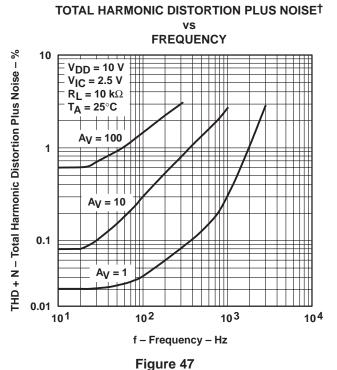
 \dagger For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.



EQUIVALENT INPUT NOISE VOLTAGE[†] **FREQUENCY** 80 V_n – Equivalent Input Noise Voltage – nV/ √Hz $V_{DD} = 3 V$ $R_S = 20 \Omega$ 70 T_A = 25°C 60 50 40 30 20 10 101 103 102 104 f - Frequency - Hz Figure 44

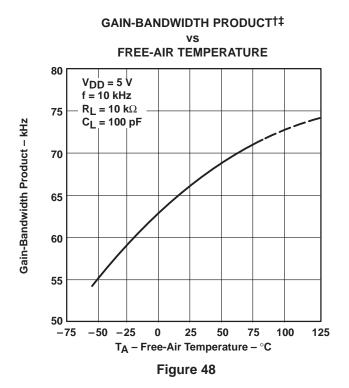


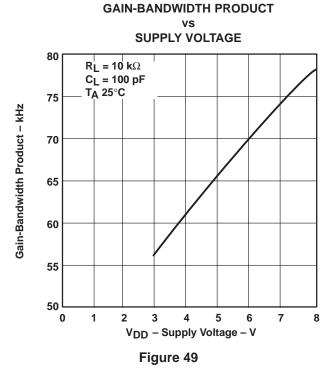


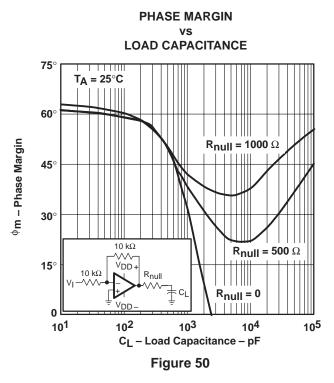


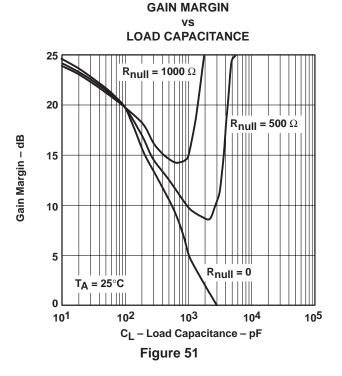
† For all curves where $V_{DD} = 5 \text{ V}$, all loads are referenced to 2.5 V. For all curves where $V_{DD} = 3 \text{ V}$, all loads are referenced to 1.5 V.











[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

[‡] For all curves where V_{DD} = 5 V, all loads are referenced to 2.5 V. For all curves where V_{DD} = 3 V, all loads are referenced to 1.5 V.



UNITY-GAIN BANDWIDTH vs

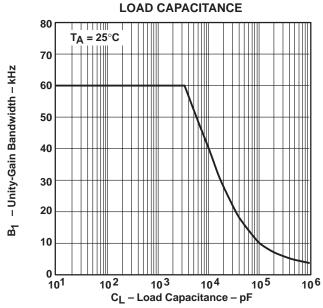


Figure 52

APPLICATION INFORMATION

driving large capacitive loads

The TLV2711 is designed to drive larger capacitive loads than most CMOS operational amplifiers. Figure 50 and Figure 51 illustrate its ability to drive loads up to 600 pF while maintaining good gain and phase margins $(R_{null} = 0)$.

A smaller series resistor (R_{null}) at the output of the device (see Figure 53) improves the gain and phase margins when driving large capacitive loads. Figure 50 and Figure 51 show the effects of adding series resistances of 500 Ω and 1000 Ω . The addition of this series resistor has two effects: the first is that it adds a zero to the transfer function and the second is that it reduces the frequency of the pole associated with the output load in the transfer function.

The zero introduced to the transfer function is equal to the series resistance times the load capacitance. To calculate the improvement in phase margin, equation 1 can be used.

$$\Delta \phi_{\text{m1}} = \tan^{-1} \left(2 \times \pi \times \text{UGBW} \times R_{\text{null}} \times C_{\text{L}} \right)$$
 (1)

Where:

 $\Delta \phi_{m1}$ = Improvement in phase margin

UGBW = Unity-gain bandwidth frequency

R_{null} = Output series resistance

 C_1 = : Load capacitance



APPLICATION INFORMATION

driving large capacitive loads (continued)

The unity-gain bandwidth (UGBW) frequency decreases as the capacitive load increases (see Figure 52). To use equation 1, UGBW must be approximated from Figure 52.

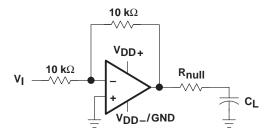


Figure 53. Series-Resistance Circuit

driving heavy dc loads

The TLV2711 is designed to provide better sinking and sourcing output currents than earlier CMOS rail-to-rail output devices. This device is specified to sink 500 μ A and source 250 μ A at V_{DD} = 3 V and V_{DD} = 5 V at a maximum quiescent I_{DD} of 25 μ A. This provides a greater than 90% power efficiency.

When driving heavy dc loads, such as $10 \text{ k}\Omega$, the positive edge under slewing conditions can experience some distortion. This condition can be seen in Figure 38. This condition is affected by three factors.

- Where the load is referenced. When the load is referenced to either rail, this condition does not occur. The distortion occurs only when the output signal swings through the point where the load is referenced. Figure 39 illustrates two $10-k\Omega$ load conditions. The first load condition shows the distortion seen for a $10-k\Omega$ load tied to 2.5 V. The third load condition shows no distortion for a $10-k\Omega$ load tied to 0 V.
- Load resistance. As the load resistance increases, the distortion seen on the output decreases. Figure 39 illustrates the difference seen on the output for a $10-k\Omega$ load and a $100-k\Omega$ load with both tied to 2.5 V.
- Input signal edge rate. Faster input edge rates for a step input result in more distortion than with slower input edge rates.



APPLICATION INFORMATION

macromodel information

Macromodel information provided was derived using Microsim Parts™, the model generation software used with Microsim PSpice™. The Boyle macromodel (see Note 6) and subcircuit in Figure 54 are generated using the TLV2711 typical electrical and operating characteristics at $T_A = 25$ °C. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification

- Unity-gain frequency
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

NOTE 6: G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, "Macromodeling of Integrated Circuit Operational Amplifiers", IEEE Journal of Solid-State Circuits, SC-9, 353 (1974).

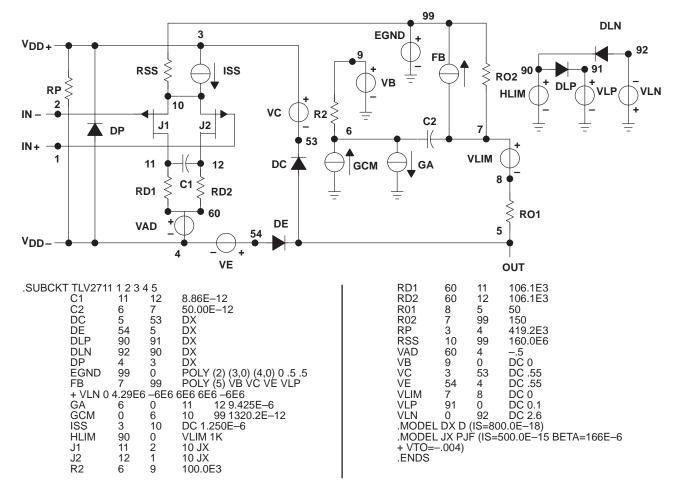


Figure 54. Boyle Macromodel and Subcircuit

PSpice and Parts are trademark of MicroSim Corporation.







17-Mar-2017

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TLV2711CDBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	VAJC	Samples
TLV2711CDBVRG4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	VAJC	Samples
TLV2711CDBVT	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		VAJC	Samples
TLV2711CDBVTG4	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		VAJC	Samples
TLV2711IDBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	VAJI	Samples
TLV2711IDBVRG4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	VAJI	Samples
TLV2711IDBVT	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		VAJI	Samples
TLV2711IDBVTG4	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM		VAJI	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



PACKAGE OPTION ADDENDUM

17-Mar-2017

- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

www.ti.com 31-Dec-2013

TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

All differsions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2711CDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV2711CDBVT	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV2711IDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV2711IDBVT	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV2711CDBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV2711CDBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
TLV2711IDBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV2711IDBVT	SOT-23	DBV	5	250	180.0	180.0	18.0

DBV (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-178 Variation AA.



DBV (R-PDSO-G5)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



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